

Product Summary

V _{(BR)DSS}	R _{DS(on)TYP}	I _D
20V	15mΩ@4.5V	7A
	18.5mΩ@2.5V	

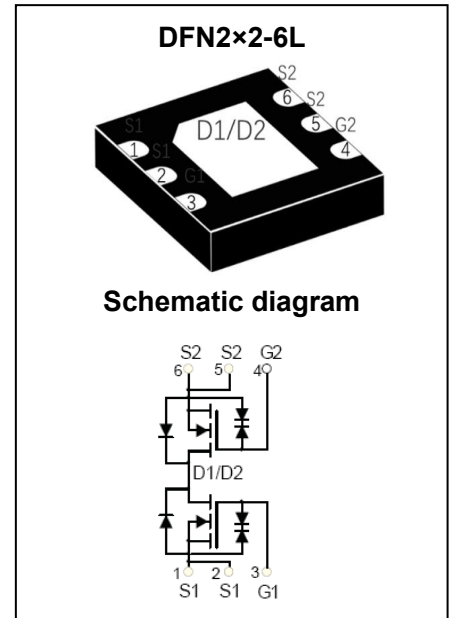
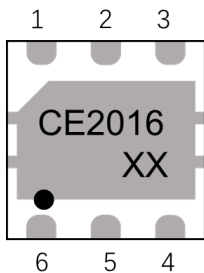
Feature

- Trench Technology Power MOSFET
- Low R_{DS(ON)}
- Low Gate Charge
- ESD Protected

Application

- Load Switch
- DC/DC Converter

MARKING:



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V _{DS}	20	V
Gate - Source Voltage	V _{GS}	±12	V
Continuous Drain Current ^{1,5}	I _D	7	A
Pulsed Drain Current ²	I _{DM}	28	A
Power Dissipation ^{4,5}	P _D	0.75	W
Thermal Resistance from Junction to Ambient ⁵	R _{θJA}	167	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

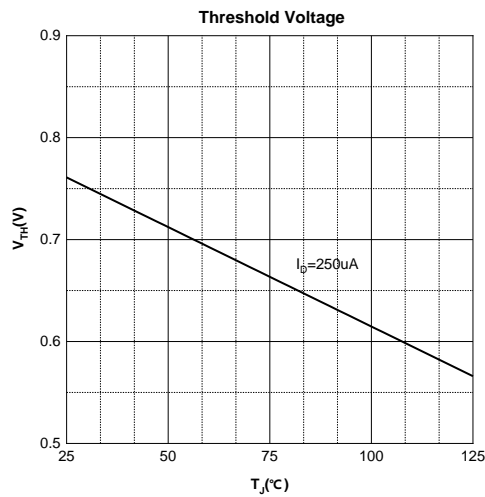
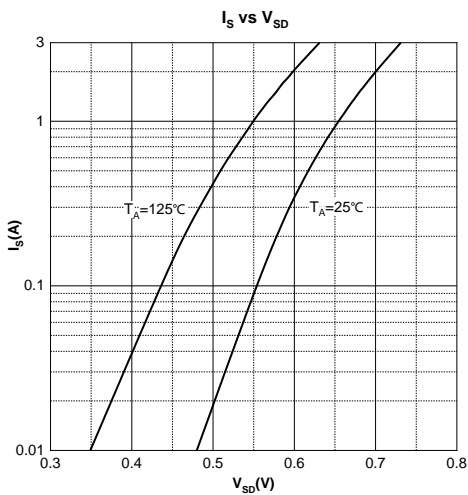
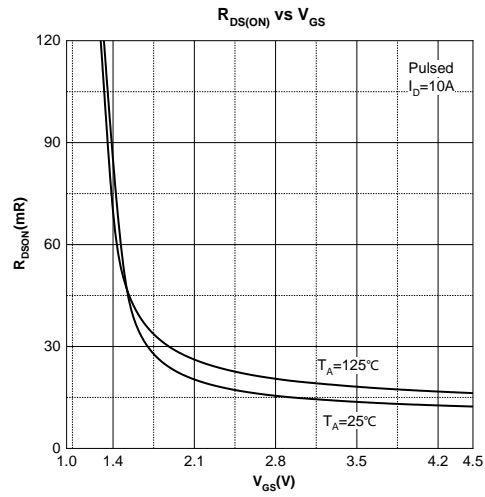
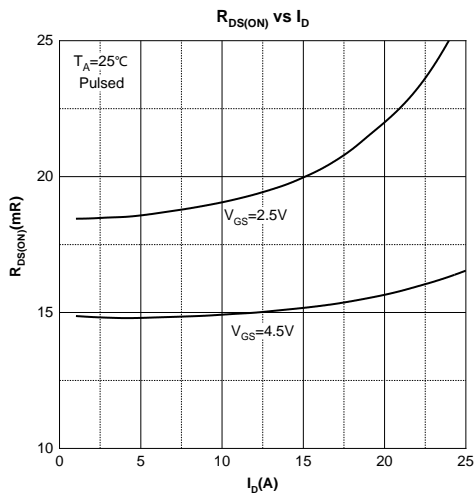
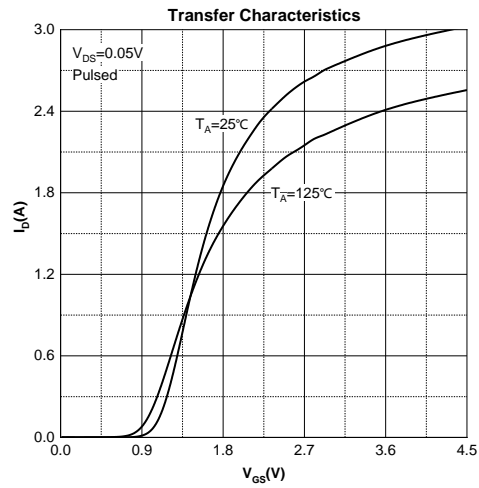
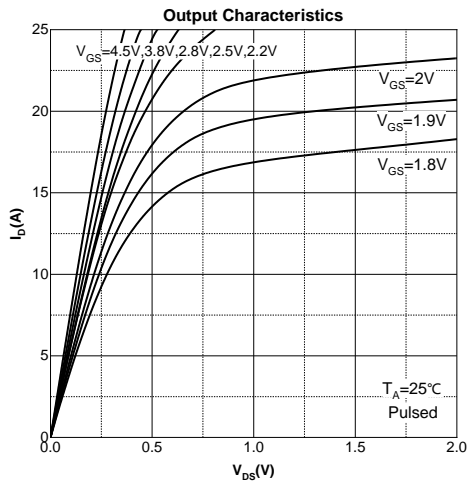
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

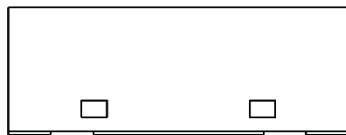
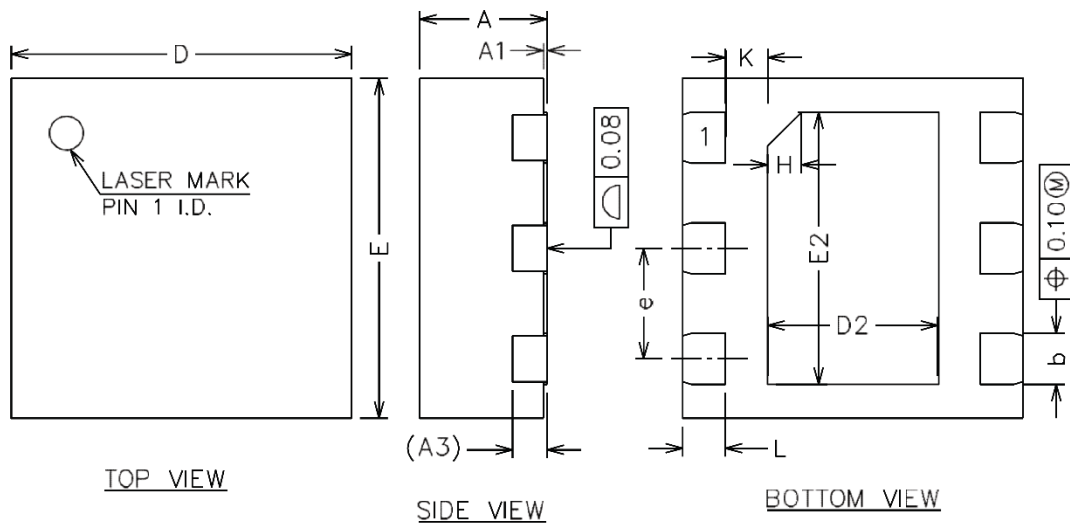
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 4	μA
On Characteristics³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5	0.75	1.1	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 3A$		15	22	m Ω
		$V_{GS} = 2.5V, I_D = 3A$		18.5	26	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 0.1MHz$		413		pF
Output Capacitance	C_{oss}			101		
Reverse Transfer Capacitance	C_{rss}			6.7		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 0.1MHz$		3636		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 10V, V_{GS} = 4.5V, I_D = 3A$		7.6		nC
Gate-source Charge	Q_{gs}			0.5		
Gate-drain Charge	Q_{gd}			2.5		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_L = 3\Omega, R_G = 3\Omega$		7		ns
Turn-on Rise Time	t_r			41		
Turn-off Delay Time	$t_{d(off)}$			18		
Turn-off Fall Time	t_f			12		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = 1A$			1.2	V

Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.
- 5.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



DFN2×2-6L Package Information


SIDE VIEW

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.527	0.577	0.021	0.023
A1	0.000	0.050	0.000	0.002
A3	0.200REF		0.008REF	
b	0.250	0.350	0.010	0.014
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
D2	0.900	1.100	0.035	0.043
E2	1.500	1.700	0.059	0.067
e	0.550	0.750	0.022	0.030
K	0.150	0.350	0.006	0.014
L	0.200	0.300	0.008	0.012
H	0.200REF		0.008REF	